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Complete if Known	
Application Number	10/081439
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First Named Inventor	Ahn, Kie
Group Art Unit	2818
Examiner Name	Unknown
Sheet 1 of 1	
Attorney Docket No: 01303.046US1	

US PATENT DOCUMENTS

Examiner Initials*	USP Document Number	Publication Date	Name of Patentee or Applicant of cited Document	Class	Subclass	Filing Date If Appropriate
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FOREIGN PATENT DOCUMENTS

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OTHER DOCUMENTS -- NON PATENT LITERATURE DOCUMENTS

Examiner Initials*	Cite No*	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T ²
DKw		GELLER, S., et al., "Crystallographic Studies of Perovskite-like Compounds. II. Rare Earth Aluminates", <u>Acta Cryst.</u> Vol. 9, (1956), pp. 1019-1025	
		GIESS, E.A., et al., "Lanthanide gallate perovskite-type substrates for epitaxial, high-T _c superconducting Ba ₂ YCu ₃ O _{7-δ} films", <u>IBM J. Res. Develop.</u> Vol. 34, No. 6, (November 6, 1990), pp. 916-926	
		LEE, A.E., et al., "Epitaxially grown sputtered LaAlO ₃ films", <u>Appl. Phys. Lett.</u> 57 (19), (November 5, 1990), pp. 2019-2021	
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DKw		MOLODYK, A. A., et al., "Volatile Surfactant-Assisted MOCVD: Application to LaAlO ₃ Thin Film Growth", <u>Chem. Vap. Deposition</u> Vol. 6, No. 3, (2000), pp. 133-138	
		PARK, BYUNG-EUN, et al., "Electrical properties of LaAlO ₃ /Si and Sr _{0.8} Bi ₂ Ta ₂ O ₉ /LaAlO ₃ /Si structures", <u>Applied Physics Letters</u> , Vol. 79, No. 6, (August 6, 2001), pp. 806-808	
		TAKEMOTO, J.H., et al., "Microstrip Resonators and Filters Using High-TC Superconducting Thin Films on LaAlO ₃ ", <u>IEEE Transaction on Magnetics</u> , Vol. 27, No. 2, (March, 1991), pp. 2549-2552	
		WILK, G.D., et al., "High- <i>k</i> gate dielectrics: Current status and materials properties considerations", <u>J. Appl. Phys.</u> , Vol. 89, No. 10, (May 15, 2001), pp. 5243-5275	

EXAMINER

Douglas W.

DATE CONSIDERED

9 Mar 04

Substitute Disclosure Statement Form (PTO-1440)

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